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UGF15A thru UGF15J

1.5A SMD Sintered Glass Passivated Junction Super Fast Recovery Rectifiers - 50V to 600V



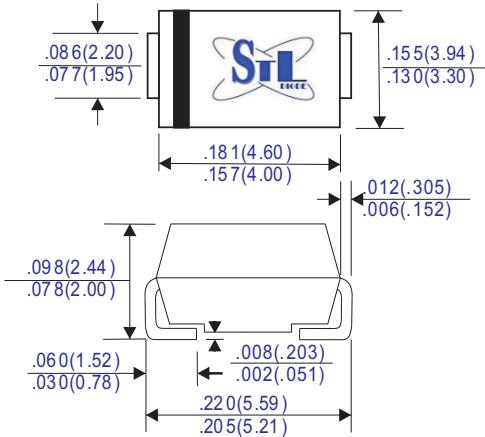
FEATURES

- High temperature metallurgically bonded construction
- Sintered glass cavity free junction
- Ideal for surface mount automotive applications
- For use in high frequency rectifier circuits
- Super fast switching for high efficiency
- High temperature soldering 450°C/5 sec at terminals
- Lead-free parts for green partner, meet environmental standards of MIL-S-19500

MECHANICAL DATA

- Case: Molded plastic SMB/DO-214AA
- Epoxy: UL94-V0 rated flame retardant
- Terminals: Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.003 ounces, 0.093 grams

SMB (DO-214AA)



Unit :inch(mm)

MAXIMUM RATING AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

| | Symbols | UGF 15A | UGF 15B | UGF 15D | UGF 15G | UGF 15J | Units |
|--|--------------------|------------|------------|------------|------------|------------|-------|
| Maximum Recurrent Peak Reverse Voltage | V _{RRM} | 50 | 100 | 200 | 400 | 600 | Volts |
| Maximum RMS Voltage | V _{RMS} | 35 | 70 | 140 | 280 | 420 | Volts |
| Maximum DC Blocking Voltage | V _{DC} | 50 | 100 | 200 | 400 | 600 | Volts |
| Maximum Average Forward Rectified Current 0.375" (9.5mm) lead length at T _L =110°C, See Figure 1 | I _{F(AV)} | | | | 1.5 | | A |
| Peak Forward Surge Current 8.3mS single half sine-wave superimposed on rated load (JEDEC Method) | I _{FSM} | | | | 50.0 | | A |
| Maximum Instantaneous Forward Voltage at 1.5A | V _F | | 0.95 | | 1.3 | 1.5 | Volts |
| Maximum DC Reverse Current at Rated DC Blocking Voltage | I _R | | | 5.0 | 100.0 | | µA |
| Typical Reverse Recovery Time (Note 1) | T _{rr} | | 35 | | 50 | | nS |
| Typical Junction Capacitance (Note 2) | C _J | | 20 | | | | pF |
| Typical Thermal Resistance (Note 3) | R _{θJA} | | 20 | | | | °C/W |
| Operating Junction Temperature Range | T _J | | -65~+175 | | | | °C |
| Storage Temperature Range | T _{STG} | | -65 ~ +175 | | | | °C |

Note 1. Reverse recovery time test conditions: I_r=0.5A, I_{rr}=1.0A, I_{RR}=0.25A

2. Measure at 1.0MHz and applied reverse voltage of 4.0Volts.

3. Thermal resistance from junction to 0.375" (9.5mm) lead length P.C.B. mounted



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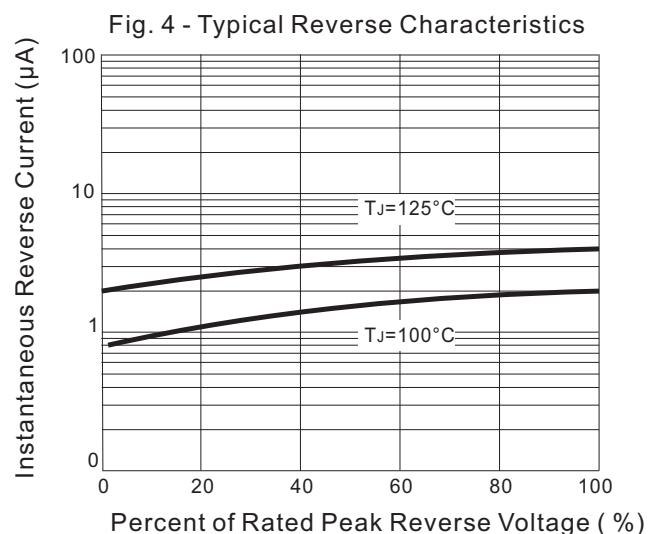
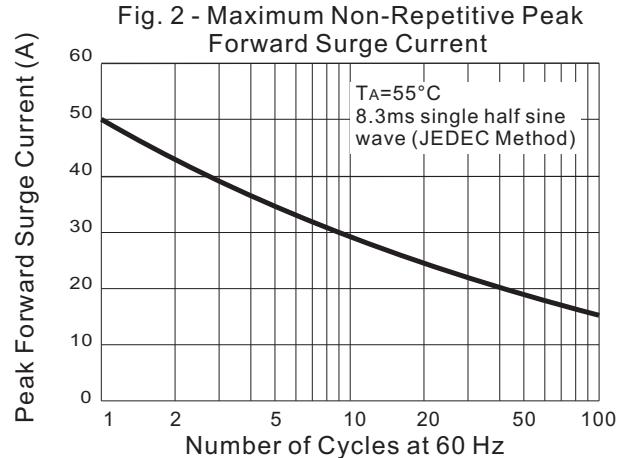
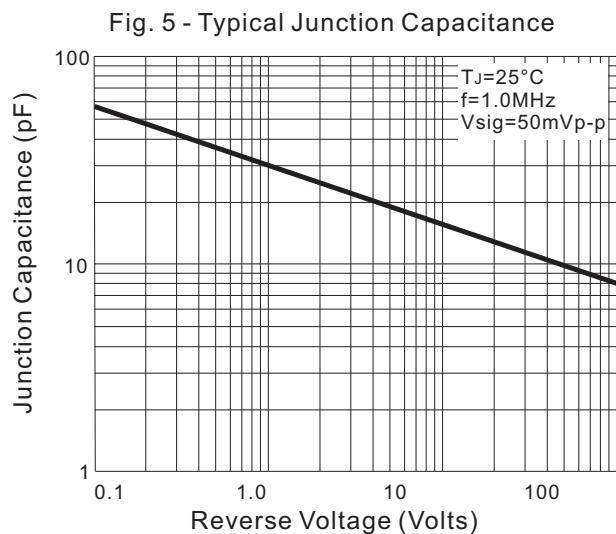
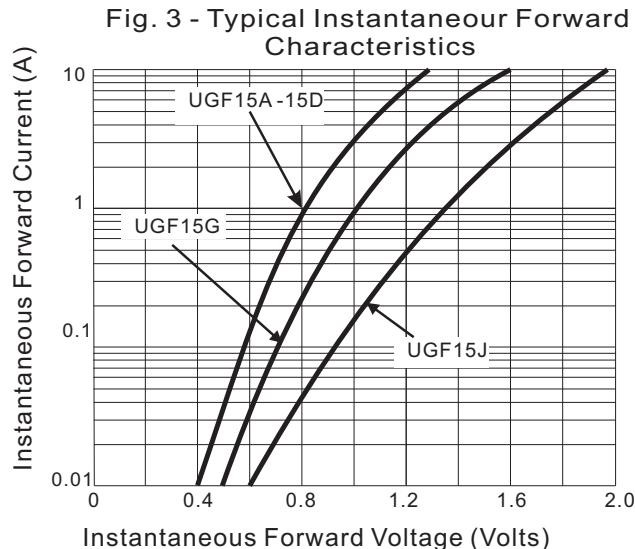
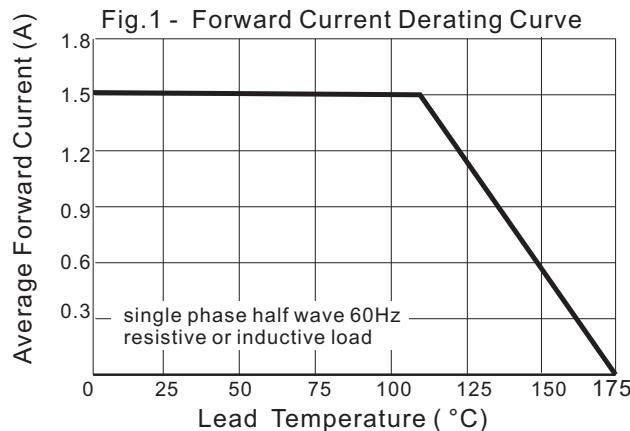
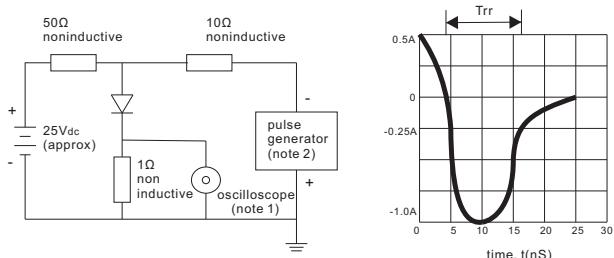


Fig. 6 - Test Circuit Diagram and Reverse Recovery Time Characteristic



Note: 1. rise time=7nS Max. input impedance=1MΩ, 22pF
2. rise time=10nS Max. source impedance=80Ω